

Docket No.: GR 96 P 8091 D2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Michael Kelly et al.  
Div. of Applic. No. : 10/324,848, filed December 20, 2002  
Div. filed : September 29, 2003  
Title : Method of Producing a Light-Emitting Diode  
Examiner : William D. Coleman                      Group Art Unit: 2823

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner for Patents;  
Alexandria, VA 22313-1450

S i r :

In accordance with 37 C.F.R. 1.98, the following patents and/or publications are cited herewith:

U.S. Patent No. 4,448,636 (Baber), dated May 15, 1984;

U.S. Patent No. 4,883,561 (Gmitter et al.), dated November 28, 1989;

German Published, Non-Prosecuted Patent Application No. DE 35 08 469 A1 (Mück et al.), dated September 11, 1986;

Published, European Patent Application No. EP 0 718 885 A2 (Gorowitz et al.), dated June 26, 1996;

M.K. Kelly et al.: "Optical Patterning of GaN films", Appl. Physics, Letter 69 (12), September 16, 1996, pp. 1749-51;

Eli Yablonovitch et al.: "Extreme Selectivity in the Lift-Off of Epitaxial GaAs films", Appl. Physics Letter 51 (26), December 28, 1987, pp. 2222-24;

R. Groh et al.: "On the Thermal Decomposition of GaN in Vacuum", pp. 353-57;

Yasua Morimoto: "Few Characteristics of Epitaxial GaN-Etching and Thermal Decomposition", J. Electrochemical Society: Solid State Science and Technology, October 1974, pp. 1383-84;

R.T. Leonard et al.: "Photoassisted Dry Etching of GaN", Appl. Physics , Letter 68, February 5, 1996, pp. 794-96;

Young-Feng Lu et al.: "Laser-Induced Dry Lift-Off Process", Jpn. J. Appl. Physics, Volume 34, 1995, pp. 1669-70;

Young-Feng Lu et al.: "Excimer-Laser Removal of SiO<sub>2</sub> Patterns from GaAs Substrates", Jpn. Appl. Physics, Volume 33, 1994, pp. 324-27.

The above-mentioned references were cited in an *Information Disclosure Statement* dated April 1, 1999, in grandparent application No. 09/283,907.

C.R. Miskys et al.: "MOCVD-Epitaxy on Free-Standing HVPE-GaN Substrates", Phys. Stat. Sol. (a) 176, 443 (1999), pp. 443-46;

L. Tsakalakos et al.: "Epitaxial Ferroelectric (Pb, La)(Zr, Ti)O<sub>3</sub> Thin Films on Stainless Steel By Excimer Laser Liftoff", Applied Physics Letters, Volume 76, No. 2, January 10, 2000, pp. 227-29.

The above-mentioned references were cited in an *Information Disclosure Statement* dated June 13, 2000, in grandparent application No. 09/283,907.

U.S. Patent No. 6,071,795 (Cheung et al.), dated June 6, 2000;

Published, European Patent Application No. EP 0 987 741 A1 (Wang et al.), dated March 22, 2000.

The above-mentioned references were cited in an *Information Disclosure Statement* dated June 22, 2000, in grandparent application No. 09/283,907.

U.S. Patent No. 3,808,550 (Ashkin), dated April 1994;

U.S. Patent No. 5,985,687 (Bowers et al.), dated November 1999;

U.S. Patent No. 6,159,824 (Henley et al.), dated December 2000.

The above-mentioned references were cited in an Office Action dated October 3, 2001, in grandparent application No. 09/283,907.

U.S. Patent No. 5,559,043 (Bruehl), dated September 1996.

The above-mentioned reference was cited in an Office Action dated April 18, 2002, in grandparent application No. 09/283,907.

U.S. Patent No. 4,846,931 (Gmitter et al.), dated July 11, 1989;

U.S. Patent No. 5,465,009 (Drabik et al.), dated November 7, 1995.

The above-mentioned references were filed in an *Information Disclosure Statement* filed September 8, 2003, in parent application No. 10/324,848.

Respectfully submitted,



For Applicants

Date: September 29, 2003

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FORM PTO-1449 (SUBSTITUTE)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: Divisional of Applic. No. GR 96 P 8091 D2      10/324,848  Applicant Michael Kelly et al.  Filing Date of Divisional      Group Art Unit September 29, 2003      2823			
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	3,808,550	04/94	Ashkin			
	B	4,448,636	05/84	Baber			
	C	4,846,931	07/89	Gmitter et al.			
	D	4,883,561	11/89	Gmitter et al.			
	E	5,465,009	11/95	Drabik et al.			
	F	5,559,043	09/96	Bruel			
	G	5,985,687	11/99	Bowers et al.			
	H	6,071,795	06/00	Cheung et al.			
	I	6,159,824	12/00	Henley et al.			
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J	DE 35 08 469 A1	09/86	Germany			
	K	EP 0 718 885 A2	06/96	Europe			
	L	EP 0 987 741 A1	03/00	Europe			
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
		M.K. Kelly et al.: "Optical Patterning of GaN films", Appl. Physics, Letter 69 (12), September 16, 1996, pp. 1749-51.					
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